

LINEAR POWER TRANSISTOR

DESCRIPTION:

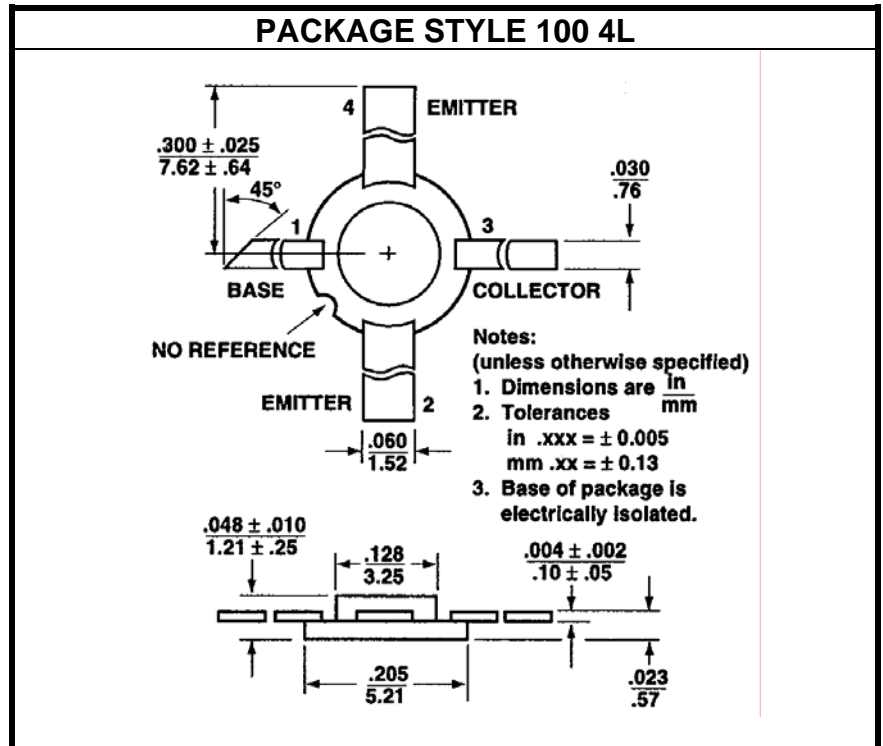
The **ASI HXTR5104** is a Common Base Device Designed for high output power and gain at VHF, UHF, and microwave frequency applications.

FEATURES INCLUDE:

- High Gain
- Hermetic package
- High power output

MAXIMUM RATINGS

I_C	250 mA
V_{CBO}	45 V
V_{CEO}	27 V
P_{DISS}	4.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	44 °C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 10$ mA	40			V
BV_{CEO}	$I_C = 50$ mA	24			V
BV_{EBO}	$I_E = 100$ μ A	3.3			V
I_{EBO}	$V_{EB} = 2.0$ V			10	μ A
I_{CES}	$V_{CE} = 32$ V			200	nA
I_{CBO}	$V_{CB} = 20$ V			100	nA
H_{FE}	$V_{CE} = 18$ V $I_C = 110$ mA	15		85	---
C_{CB}	$V_{CB} = 10$ $f = 1.0$ MHz		0.70		pF
P_{1dB}		28	29		dBm
G_{1dB}	$V_{CE} = 18$ V $I_C = 110$ mA $f = 2.0$ GHz	8.0	9.0		dBm
η			35		%